IHSM33R020F2

V_{DSS}	3300 V
$R_{DS(on)}$	20 mΩ

HAWKPACK PF2 series

3300 V, 20 mΩ, Silicon Carbide, Full-bridge Module



Press-fit low-profile, large

Features

- Complete H-bridge in one module
- Baseplate-less, press-fit pins
- Short commutation loops for fast switching

Typical applications

- Medium-voltage modular converters
- Two-level conversion on 2000 V and higher DC buses
- Grid-tied and renewable energy converters

Description

3300 V, 20 mΩ silicon-carbide MOSFET full-bridge module in a 62.8 × 56.7 mm baseplate-less housing.

Key specifications

Parameter	Value
V_{DSS}	3300 V
$R_{DS(on)}$ typ., T_{vj} = 25 °C	20 mΩ
I_D nominal	100 A
Topology	Full-bridge
T_{vj} op. max	175 °C
Outline	62.8 × 56.7 mm, baseplate-less, press-fit pins

Full characterization data

Thermal resistance, switching energies and times, capacitances, gate charge and typical characteristic curves for IHSM33R020F2 are available on request: request the full data or write to sales@ironhawksemi.com.

Package

Press-fit low-profile, large. Mechanical outline drawing, STEP model and PCB footprint available on request.

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Ordering information

Part number	Packing	MOQ	Lead time
IHSM33R020F2	Box	On request	On request

Information in this document is believed to be accurate but is subject to change without notice. Typical values are not guaranteed. The customer is responsible for validating suitability in the end application. IRONHAWK · sales@ironhawksemi.com

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